



### INTRODUCE:

HVGT high voltage silicon rectifier assembly is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

### FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

### APPLICATIONS:

1. Power doubler circuit.
2. Power supply of laser equipment .
3. General purpose high voltage rectifier.
4. Other.

### MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 5.5 grams (approx).

### SHAPE DISPLAY:

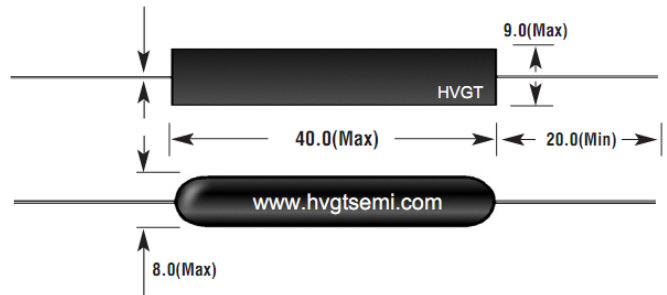


SIZE: (Unit:mm)

HVGT NAME: HVS-080940H

### HVS-080940H Series

Lead Diameter 1.0mm



Unit:mm

### MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_A=25^{\circ}C$	20	kV
Average Forward Current Maximum	$I_{FAVM}$	$T_A=40^{\circ}C$	100	mA
Suege Current	$I_{FSM}$	$T_A=25^{\circ}C$ ; Half-Sine Wave; 8.3mS	3.0	A
Junction Temperature	$T_J$		125	$^{\circ}C$
Allowable Operation Case Temperature	$T_C$		-40~+125	$^{\circ}C$
Storage Temperature	$T_{STG}$		-40~+125	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	$V_F$	at $25^{\circ}C$ ; at $I_{F(AV)}$	24	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ ; at $V_{RRM}$	2.0	$\mu A$
	$I_{R2}$	at $100^{\circ}C$ ; at $V_{RRM}$	50	$\mu A$
Maximum Reverse Recovery Time	$T_{RR}$	at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	$C_J$	at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$	--	pF



Fig 1

Forward Current Derating Curve

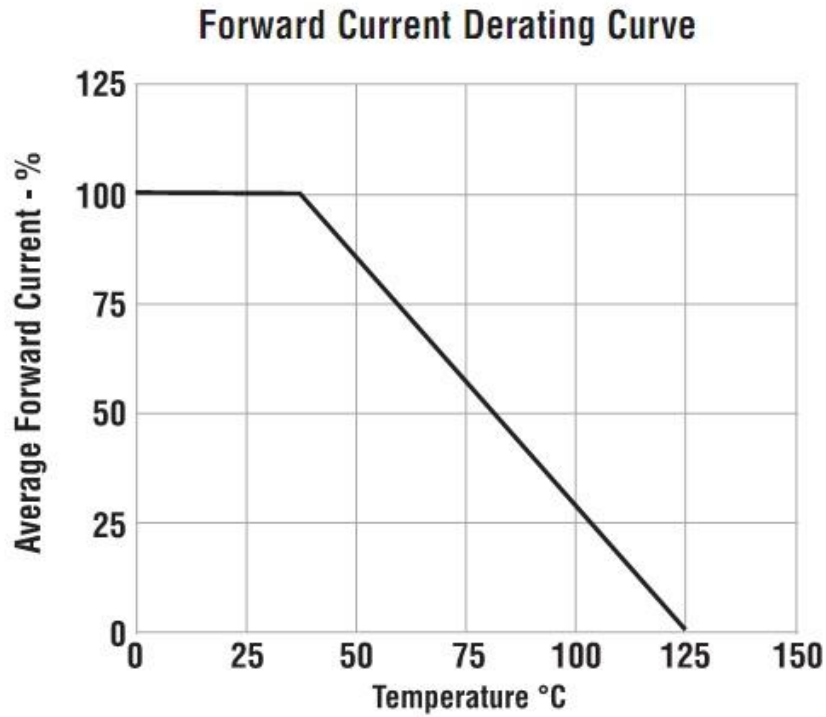


Fig 2

Non-Repetitive Surge Current

